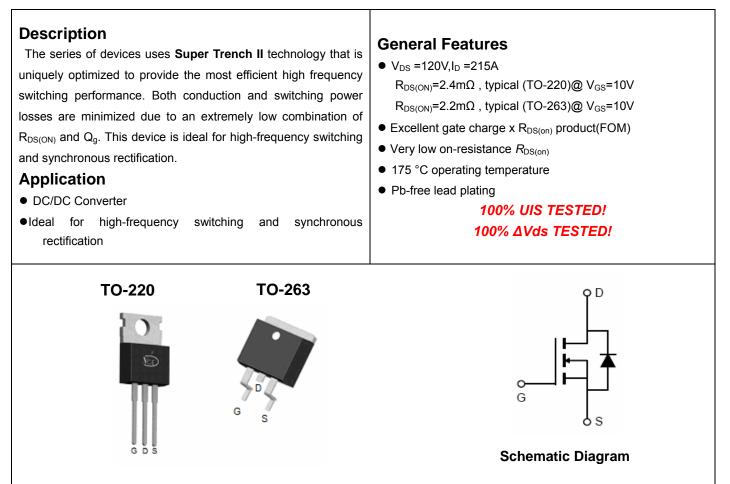


NCE N-Channel Super Trench II Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP030N12	NCEP030N12	TO-220	-	-	-
NCEP030N12D	NCEP030N12D	TO-263			

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	120	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	215	А
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	150	А
Pulsed Drain Current	I _{DM}	860	А
Maximum Power Dissipation	PD	340	W
Derating factor		2.27	W/℃
Single pulse avalanche energy (Note 4)	E _{AS}	2332	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C



0.44

R_{ejc}

Thermal Characteristic

Thermal Resistance, Junction-to-Case

°C/W

Electrical Characteristics (T_c=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 2)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA		2.0	3.0	4.0	V
Drain-Source On-State Resistance	Desserve		TO-220	-	2.4	3.0	mΩ
	R _{DS(ON)}	V _{GS} =10V, I _D =107.5A	TO-263		2.2	3.0	
Forward Transconductance	g fs	V _{DS} =5V,I _D =107.5A			200	-	S
Dynamic Characteristics (Note3)							
Input Capacitance	C _{lss}	- V _{DS} =60V,V _{GS} =0V, - F=1.0MHz		-	15500	-	PF
Output Capacitance	Coss			-	1020	-	PF
Reverse Transfer Capacitance	Crss			-	23	-	PF
Switching Characteristics (Note 3)							
Turn-on Delay Time	t _{d(on)}			-	37	-	nS
Turn-on Rise Time	tr	V _{DD} =60V,I _D =107.5A V _{GS} =10V,R _G =1.6Ω		-	29	-	nS
Turn-Off Delay Time	t _{d(off)}			-	82	-	nS
Turn-Off Fall Time	t _f			-	34	-	nS
Total Gate Charge	Qg	- V _{DS} =60V,I _D =107.5A, - V _{GS} =10V		-	225	-	nC
Gate-Source Charge	Q _{gs}			-	73		nC
Gate-Drain Charge	Q _{gd}			-	50		nC
Drain-Source Diode Characteristics	·					. 1	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =107.5A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	215	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 107.5A		-	105	-	nS
Reverse Recovery Charge	Qrr	di/dt = $100A/\mu s^{(Note2)}$		-	290	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

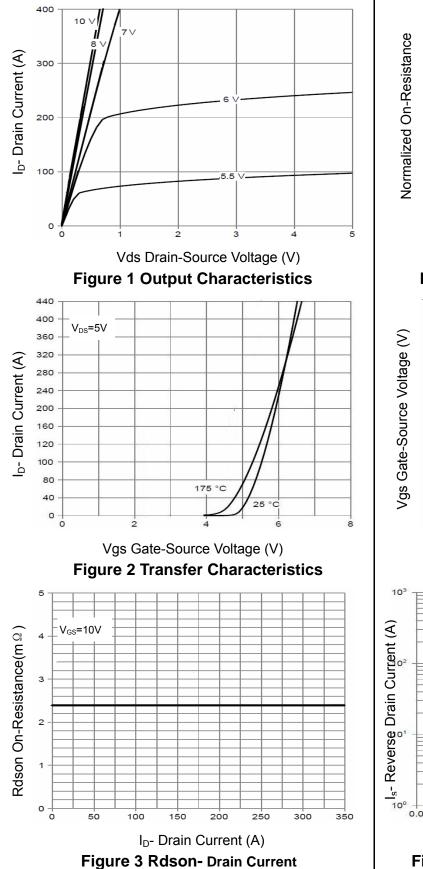
2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

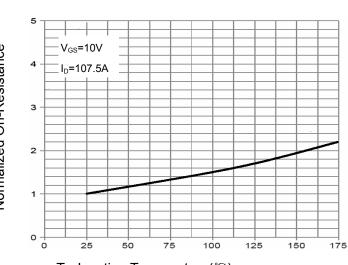
3. Guaranteed by design, not subject to production

4. EAS condition : Tj=25 $^\circ \!\! C$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω



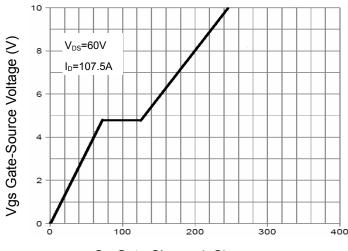
Typical Electrical and Thermal Characteristics





 T_J -Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



Qg Gate Charge (nC) Figure 5 Gate Charge

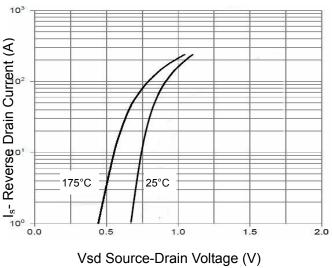
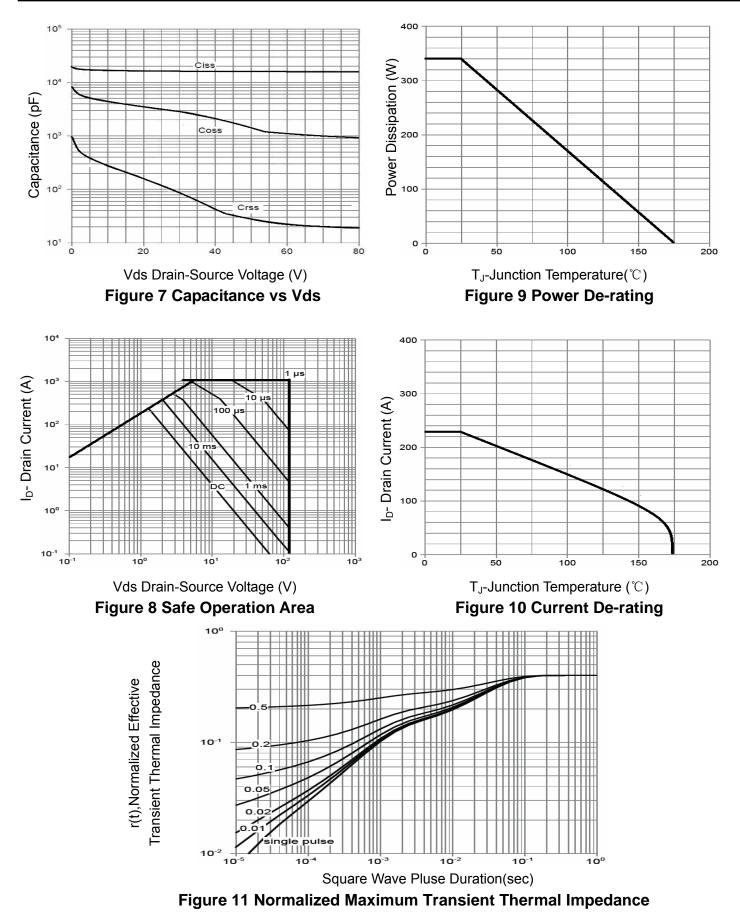


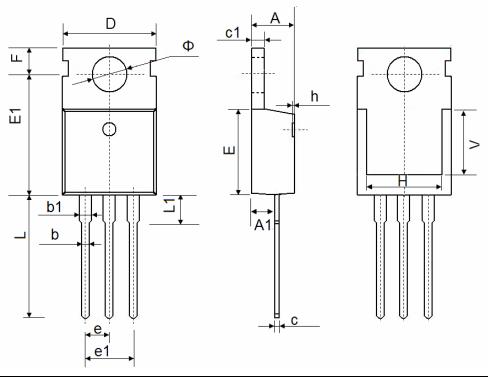
Figure 6 Source- Drain Diode Forward







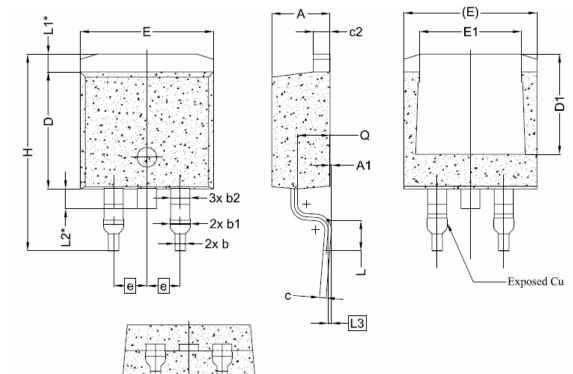
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
e	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Φ	3.400	3.800	0.134	0.150	

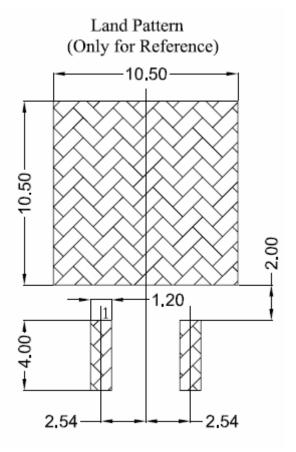


TO-263-2L Package Information



Symbol	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
A	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.45	1.70		
с	0.40	0.50	0.60		
c2	1.15	1.27	1.40		
D	8.82	8.92	9.02		
D1	6.86	7.65	-		
E	9.96	10.16	10.36		
E1	6.89	7.77	7.89		
е	2.54BSC				
Н	14.61	15.00	15.88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48	2.70		





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